

L Number	Hits	Search Text	DB	Time stamp
2	5	((("6261876") or ("5970339") or ("5789305") or ("5494846") or ("5413953"))).PN.	USPAT	2004/03/04 21:07
6	5071	((438/149) or (438/311) or (438/423) or (438/425) or (438/426) or (438/443) or (438/444) or (438/439) or (257/7) or (257/8) or (257/499) or (257/500) or (257/501) or (257/506)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:40
7	32097	soi or (semiconductor near2 insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:42
8	78634	trench or trenches	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:42
9	373057	(insulate or insulating or insulation) near (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:43
10	2960	bulk near semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:43
12	6717	(soi or (semiconductor near2 insulator)) and (trench or trenches)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:44
13	3935	((soi or (semiconductor near2 insulator)) and (trench or trenches)) and ((insulate or insulating or insulation) near (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:44
14	3935	((((soi or (semiconductor near2 insulator)) and (trench or trenches)) and ((insulate or insulating or insulation) near (layer or film))) and ((insulate or insulating or insulation) near (layer or film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:44
15	239	(((((soi or (semiconductor near2 insulator)) and (trench or trenches)) and ((insulate or insulating or insulation) near (layer or film))) and ((insulate or insulating or insulation) near (layer or film))) and (bulk near semiconductor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:44
16	0	(((((soi or (semiconductor near2 insulator)) and (trench or trenches)) and ((insulate or insulating or insulation) near (layer or film))) and ((insulate or insulating or insulation) near (layer or film))) and (bulk near semiconductor)) and (monolithic same intergrated)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:44
17	76883	monolithic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:45
19	4	(((((soi or (semiconductor near2 insulator)) and (trench or trenches)) and ((insulate or insulating or insulation) near (layer or film))) and ((insulate or insulating or insulation) near (layer or film))) and (bulk near semiconductor)) and monolithic) and (((438/149) or (438/311) or (438/423) or (438/425) or (438/426) or (438/443) or (438/444) or (438/439) or (257/7) or (257/8) or (257/499) or (257/500) or (257/501) or (257/506)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:45

11	44	monolithic same intergrated	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:46
18	28	((((soi or (semiconductor near2 insulator)) and (trench or trenches)) and ((insulate or insulating or insulation) near (layer or film))) and ((insulate or insulating or insulation) near (layer or film))) and (bulk near semiconductor)) and monolithic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:48
-	1	("6613639").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/02 14:16